## Dose Dependent Structural Properties of Fe Ion Implanted CuInSe<sub>2</sub> Thin Film

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The I-III-VI<sub>2</sub> compound are the most promising thin film photovoltaic cell. Because of their highest absorption coefficient and the best thermal stability, CuInSe<sub>2</sub> thin film solar cells are the most popular material applied in photovoltaic cells. Based on the band structure simulation of the Fe doped CuInSe<sub>2</sub> [1], it is believed the generated photocurrent and the output voltage of the operating cells will be higher.

The CuInSe<sub>2</sub> thin films were prepared by an MBE system. The concentrations of implanted Fe were from  $2*10^{14}$  to  $1*10^{17}$  (cm<sup>-2</sup>) at 72 keV. The annealing process was taken under  $6.2*10^{-2}$  torr at 400 °C.

From the X-ray diffraction spectra (see Fig.1), there is no detectable secondary phases in all the dose of CuInSe<sub>2</sub> samples and also no Fe clusters segregated on the surface of the CuInSe<sub>2</sub> thin film. From the enlarged spectra, the peak shifts were observed at [312] diffraction peaks. It may indicate that the iron atoms would replace the copper atom sites because of the shorten d-spacing of lattice plane, [312].

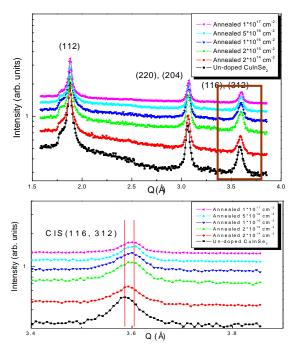


Figure 1. X-ray diffraction spectra of all implnated samples

Fig 2 shows the d-spacing was decreased as the implanted dose increased. It might indicate that the iron atoms of high dose implanted iron atoms would be segregated. From the X-ray absorption spectra (Fig. 3), the energy of absorption edge indicates that the valence state of iron atoms in light dose implanted CuInSe<sub>2</sub> thin

films is +2. We can speculate that the light dose implanted iron atoms might form the Fe<sub>Cu</sub> substitutional atoms. Fig. 4 shows the X-ray absorption spectra of Fe K-edge at high dose. The valence state of iron of high dose implanted CuInSe<sub>2</sub> thin film is 0. It means that the iron atoms segregated from CuInSe<sub>2</sub> matrix and form iron clusters.

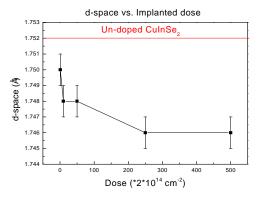
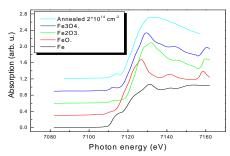
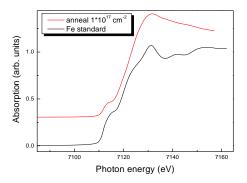


Figure 2. The variation of d-spacing of lattice plane, [312]



**Figure 3.** The X-ray absorption spectra of iron of  $2*10^{16}$  cm<sup>-2</sup> Fe implanted CuInSe<sub>2</sub> thin film.



**Figure 4.** The X-ray absorption spectra of the Fe K-edge of the high dose  $(1*10^{17} \text{ cm}^{-2})$  implanted CuInSe<sub>2</sub> thin film.

[1] Jean-Marc Raulot, Christophe Domain, and Jean-François Guillemoles, Phys. Rev. B **71**, 035203 (2005).